RoHS

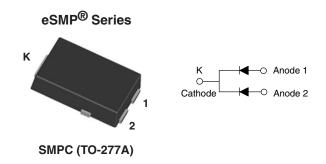
COMPLIANT

HALOGEN FREE



## Vishay Semiconductors

# Hyperfast Rectifier, 2 x 4 A FRED Pt®



#### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	2 x 4 A			
$V_R$	200 V			
V <sub>F</sub> at I <sub>F</sub>	0.72 V			
t <sub>rr (typ.)</sub>	25 ns			
T <sub>J</sub> max.	175 °C			
Package	SMPC (TO-277A)			
Circuit configuration	Common cathode			

#### **FEATURES**

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

#### **MECHANICAL DATA**

Case: SMPC (TO-277A)

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V <sub>RRM</sub>		200	V
Average rectified forward current	per device	· I <sub>F(AV)</sub>	T <sub>Sp</sub> = 160 °C	8	
Average rectilled forward current	per diode			4	۸
Non-repetitive peak surge current -	per device		T <sub>.1</sub> = 25 °C	130	А
	per diode	IFSM	1J = 25 G	70	
Operating junction and storage tem	nperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$	I <sub>R</sub> = 100 μA	200	-	-	
Commend welfage and display	V	I <sub>F</sub> = 4 A	-	0.89	0.95	V
Forward voltage, per diode	V <sub>F</sub>	I <sub>F</sub> = 4 A, T <sub>J</sub> = 150 °C	-	0.72	0.78	
Reverse leakage current, per diode		$V_R = V_R$ rated	-	-	2	
neverse leakage current, per diode	I <sub>R</sub>	T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	6	80	μΑ
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	17	-	pF



# Vishay Semiconductors

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
			$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		25	-	
Payaraa raaayany tima	t <sub>rr</sub>	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	1	25	
Reverse recovery time t <sub>rr</sub>		T <sub>J</sub> = 25 °C		-	18	-	ns
		T <sub>J</sub> = 125 °C		-	27	-	
Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	$I_F = 4 A$ $dI_F/dt = 200 A/\mu s$ $V_B = 160 V$	=	2	-	Α	
	T <sub>J</sub> = 125 °C		=	3.6	-	_ ^	
D	0	T <sub>J</sub> = 25 °C		-	18	-	nC
neverse recovery charge	Reverse recovery charge Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	50	-	IIC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistance, junction to mount, per leg	R <sub>thJM</sub>		-	2.5	3.5	°C/W
Thermal resistance, junction to ambient, per leg	R <sub>thJA</sub>		-	80	-	°C/W
Approximate weight				0.1		g
Approximate weight				0.0035		OZ.
Marking device		Case style SMPC (TO-277A)		QC	CH2	

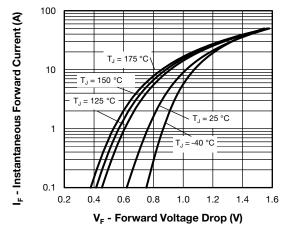


Fig. 1 - Typical Forward Voltage Drop Characteristics

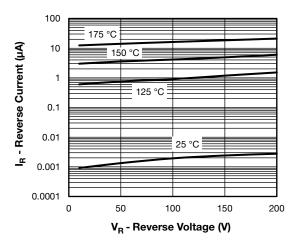


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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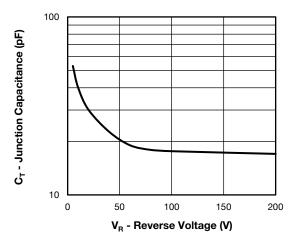


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

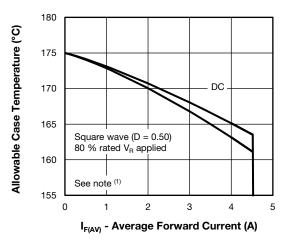


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

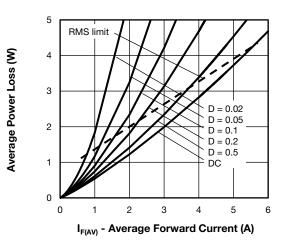


Fig. 5 - Forward Power Loss Characteristics

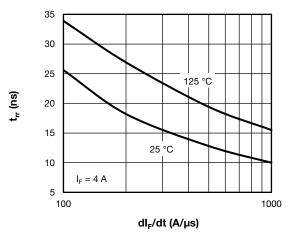


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

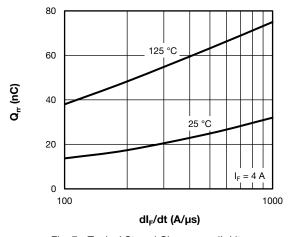


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $<sup>\</sup>begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D)}; I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 

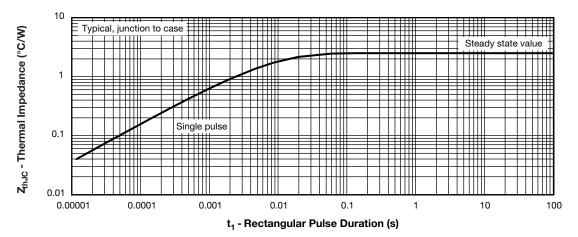


Fig. 8 - Typical Transient Thermal Impedance, Junction to Case

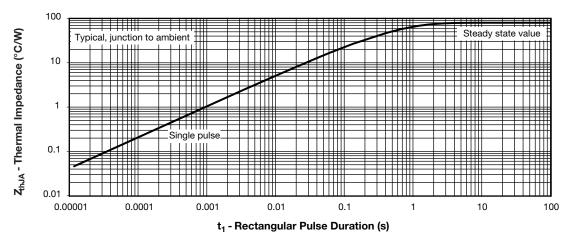
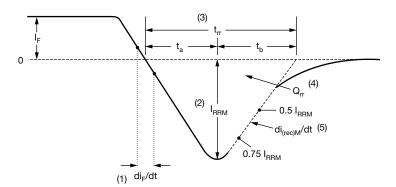


Fig. 9 - Typical Transient Thermal Impedance, Junction to Ambient



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{\text{RRM}}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

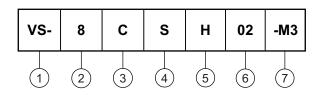
Fig. 10 - Reverse Recovery Waveform and Definitions



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### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating (8 = 8 A)

**3** - Circuit configuration:

C = common cathode

- S = SMPC package

5 - Process type,

H = hyper fast recovery

6 - Voltage code (02 = 200 V)

7 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-8CSH02-M3/86A	1500	1500	7" diameter plastic tape and reel		
VS-8CSH02-M3/87A	6500	6500	13" diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95570			
Part marking information	www.vishay.com/doc?95565			
Packaging information	www.vishay.com/doc?88869			
SPICE model	www.vishay.com/doc?96095			



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# **SMPC (TO-277A)**

### **DIMENSIONS** in inches (millimeters)





### **Legal Disclaimer Notice**

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